

OCT 27 2005

I hereby certify that this correspondence is being facsimile transmitted to the Patent and Trademark Office, facsimile no. (571) 273-8300, on the date shown below.

Dated: October 27, 2005

Signature:

Diane R. Lytle
(Diane R. Lytle)

Docket No.: 65306-0094
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Xiaojun Weng et al.

Application No.: 10/706,737

Confirmation No.: 7548

Filed: November 12, 2003

Art Unit: 2822

For: NARROW ENERGY BAND GAP GALLIUM
ARSENIDE NITRIDE SEMI-CONDUCTORS
AND AN ION-CUT-SYNTHESIS METHOD
FOR PRODUCING THE SAME

Examiner: K. M. Picardat

AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated June 30, 2005, please amend the above-identified U.S. patent application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 6 of this paper.